

**PATENT APPLICATION**  
Attorney Docket No.: 2000.008.00/US

Substitute for form 1449A/PTO				<b>Complete If Known</b>	
				Application Number	10/620887
				Filing Date	September 25, 2003
				First Named Inventor	Kevin J. Yang
				Art Unit	2813
				Examiner Name	WU JIE CHOW TCZ
SHEET	1	OF	1	Attorney Docket Number	2000.008.00/US

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No.1	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number- Kind Code (If known)			
EDJ		US 6,462,359	10-08-02	Nemati et al.	—
		US 6,229,161	05-08-01	Nemati et al.	—
EDJ		US 4,323,793	04-06-82	Schutten et al.	—

**OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T2
EDJ		S. Lombardo et al., High Temperature Annealing Effects on the Electrical Characteristics of C Implanted Si; J. Appl. Phys. Vol. 79, No. 7, pp. 34643469, April 1, 1996.	
		Ibrahim Ban et al.; Effects of Carbon Implantation on Generation Lifetime in Silicon; Appl. Phys. Lett.; Vol. 68, No. 4, pp. 499-501, Jan. 22, 1996.	
		American Microsemiconductor, Tunnel Diode and Back Diode Tutorial; at <a href="http://www.americanmicrosemi.com/tutorials/tunneldiode.htm">www.americanmicrosemi.com/tutorials/tunneldiode.htm</a> ; July 31, 2003.	
EDJ		Alan SEABAUGH; Silicon-Based Tunnel Diodes and integrated Circuits; University of Notre Dame; at <a href="http://www.nd.edu/~nano/0a1003QFDpaper_v1.pdf">http://www.nd.edu/~nano/0a1003QFDpaper_v1.pdf</a> ; July 31, 2003.	

Examiner Signature	<i>EDJ</i>	Date Considered	7-1-05
--------------------	------------	-----------------	--------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 801.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. 6 Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.